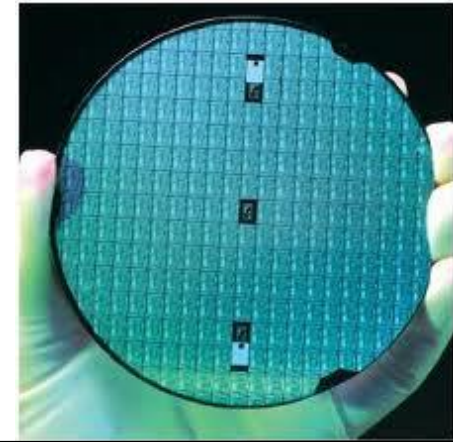
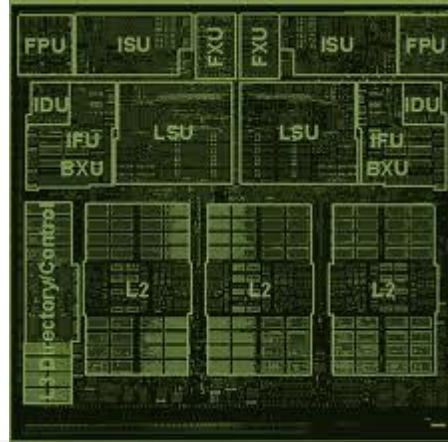
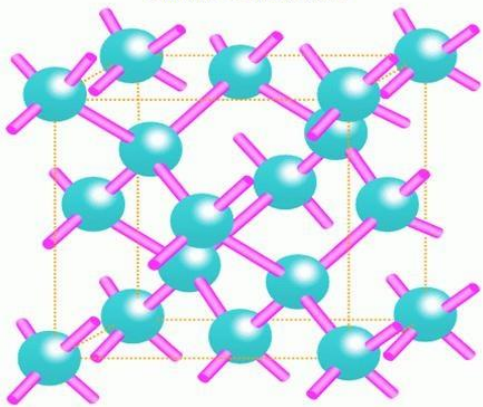


Structure of silicon crystal



ECE 122A

VLSI Principles

Lecture 3

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2-input NOR Gate

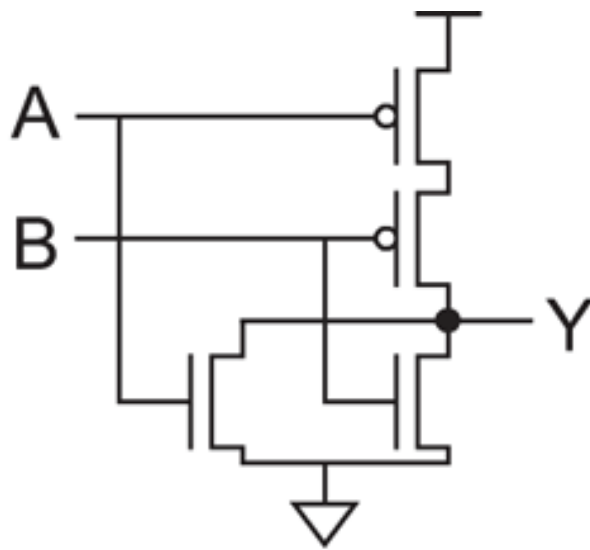
$$2\text{-input NOR: } Y = \overline{A + B} = \overline{A} \cdot \overline{B}$$

Table 1.4		NOR gate truth table	
A	B	Y	
0	0	1	
0	1	0	
1	0	0	
1	1	0	

2 PMOS must be in series.....

2 NMOS must be in parallel....

CMOS NOR Implementation



(a)



(b)

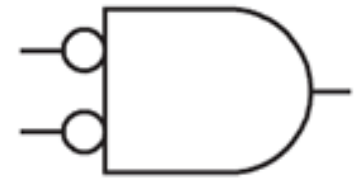


FIG 1.15 2-input NOR gate schematic (a) and symbol (b) $Y = \overline{A + B}$

CMOS 3-input NOR Implementation

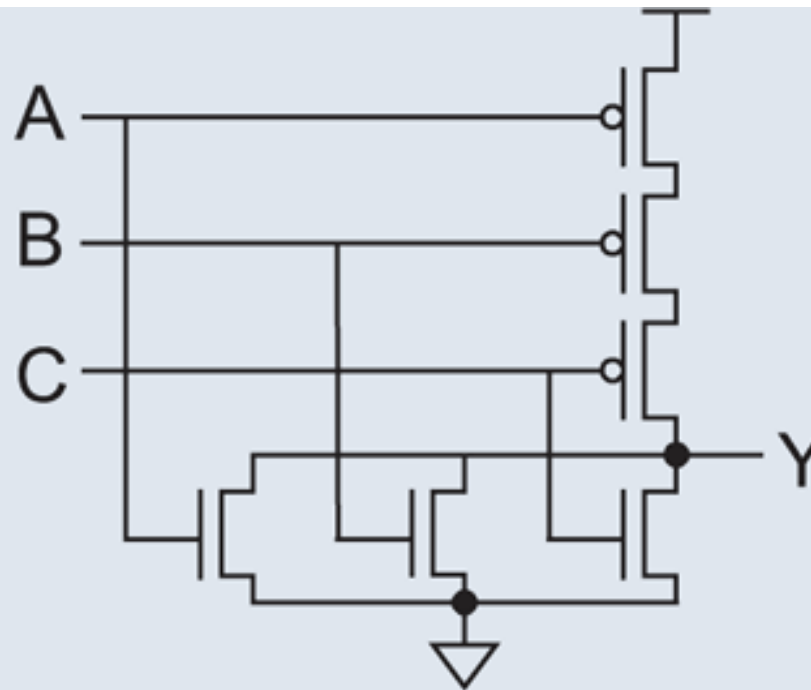
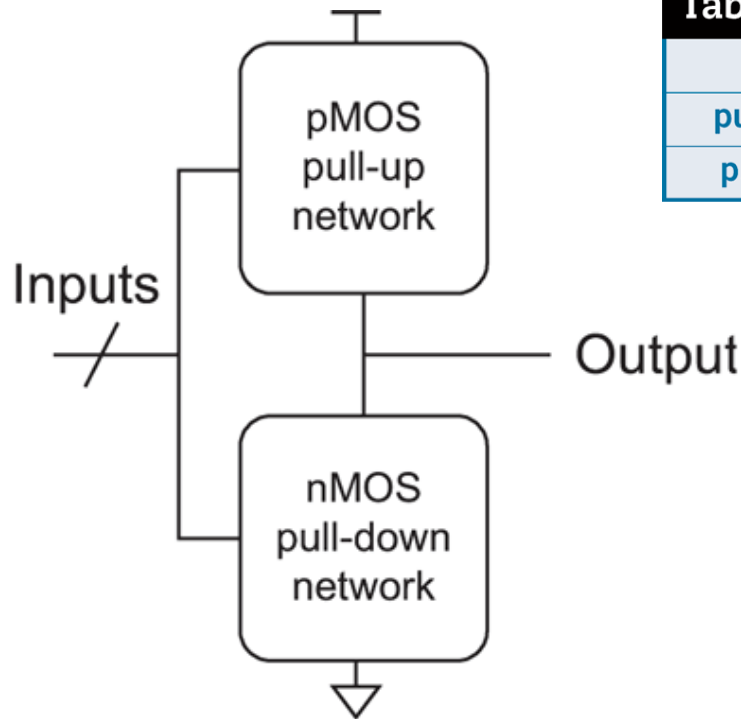


FIG 1.16 3-input NOR gate schematic
$$Y = \overline{A + B + C}$$

Combinational Logic



	pull-up OFF	pull-up ON
pull-down OFF	Z	1
pull-down ON	0	crowbarred (X)

Output state X should always be avoided: static power

Output state Z indicates a high-impedance state. If a gate's output state = Z, that gate has no influence on the rest of the circuit

Z-state is used in tri-state logic circuits and is of relevance in certain gates such as multiplexers

FIG 1.13 General logic gate using pull-up and pull-down networks

Compound Gates

$$Y = \overline{A.B + C.D}$$

Needs 20 transistors....

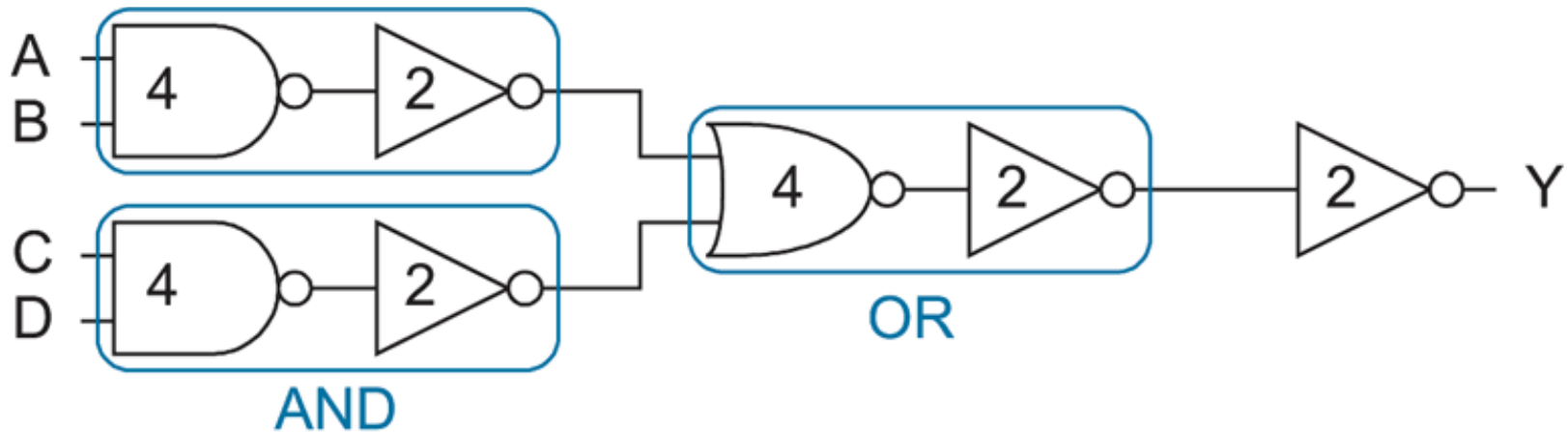
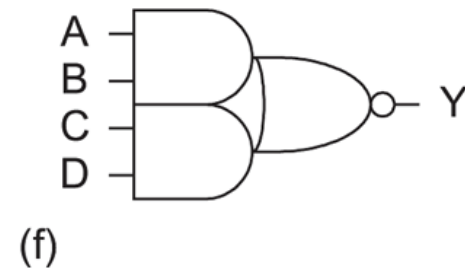
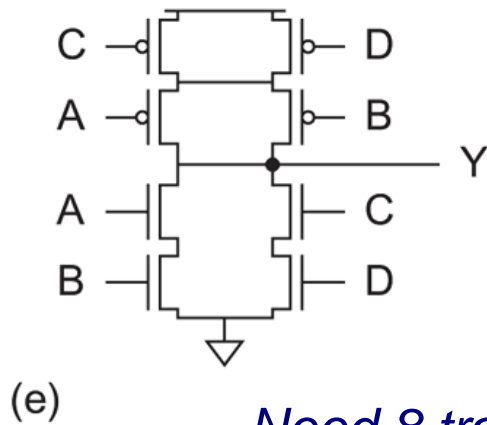
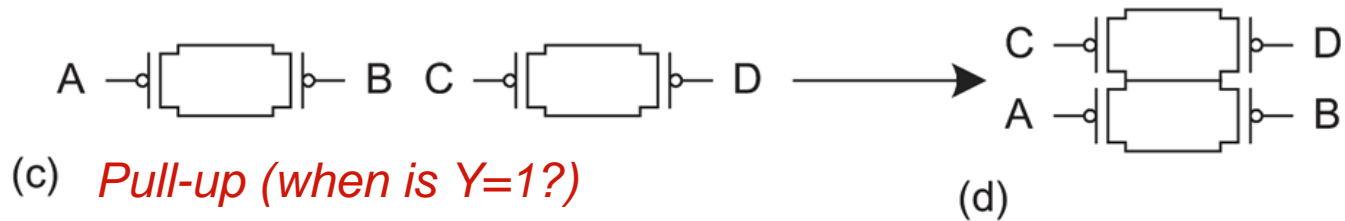
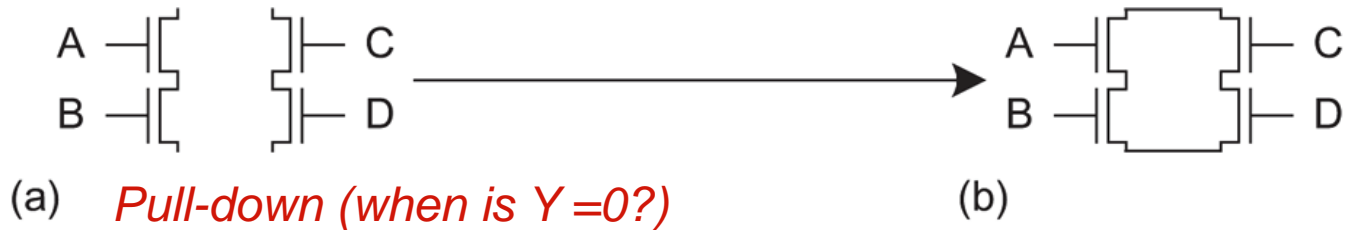


FIG 1.23 Inefficient discrete gate implementation of AOI22 indicating transistor counts

Compound Gates $Y = \overline{A.B + C.D}$



Compound Gates

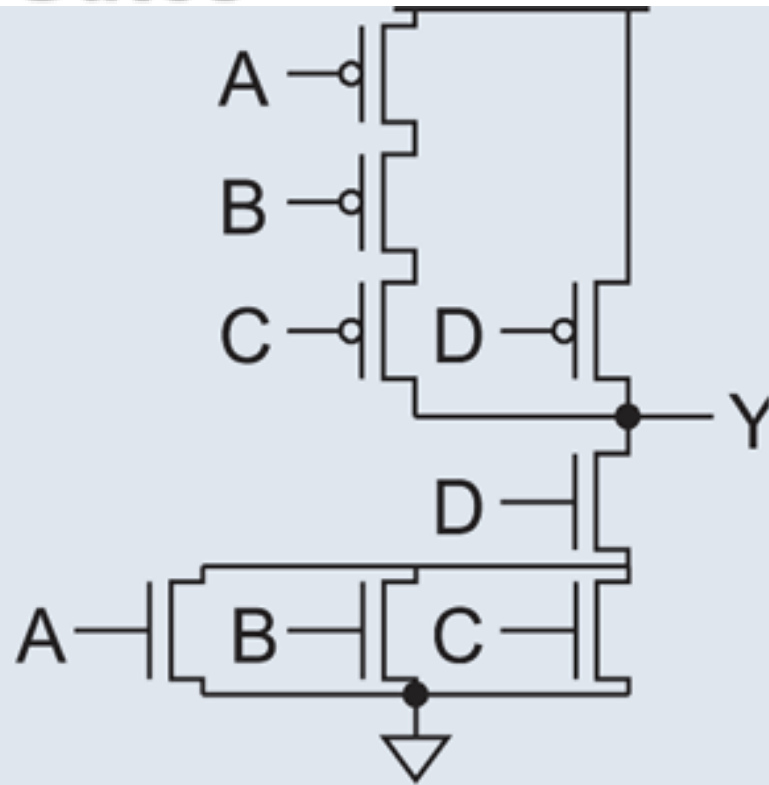


FIG 1.18 CMOS compound gate for function $Y = \overline{(A + B + C)} \cdot D$

Pass Transistors

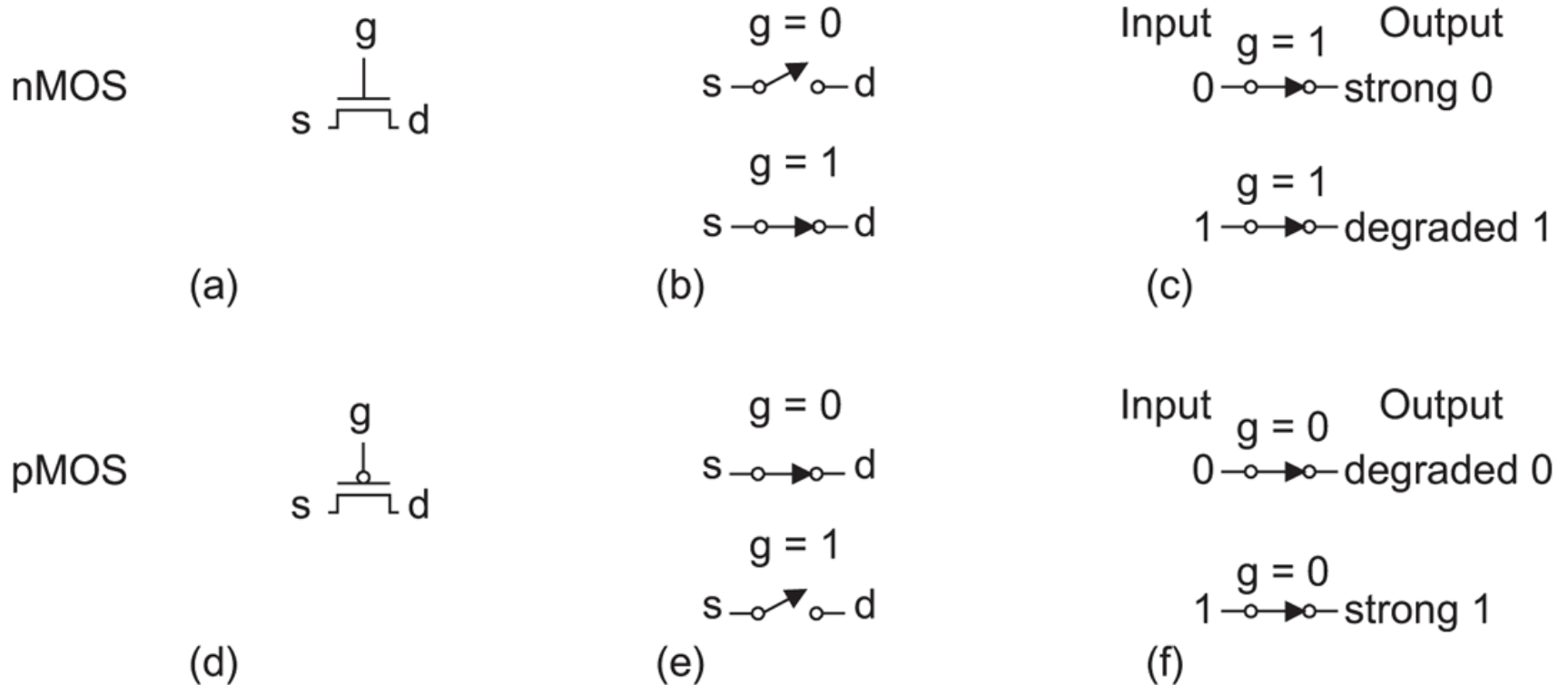
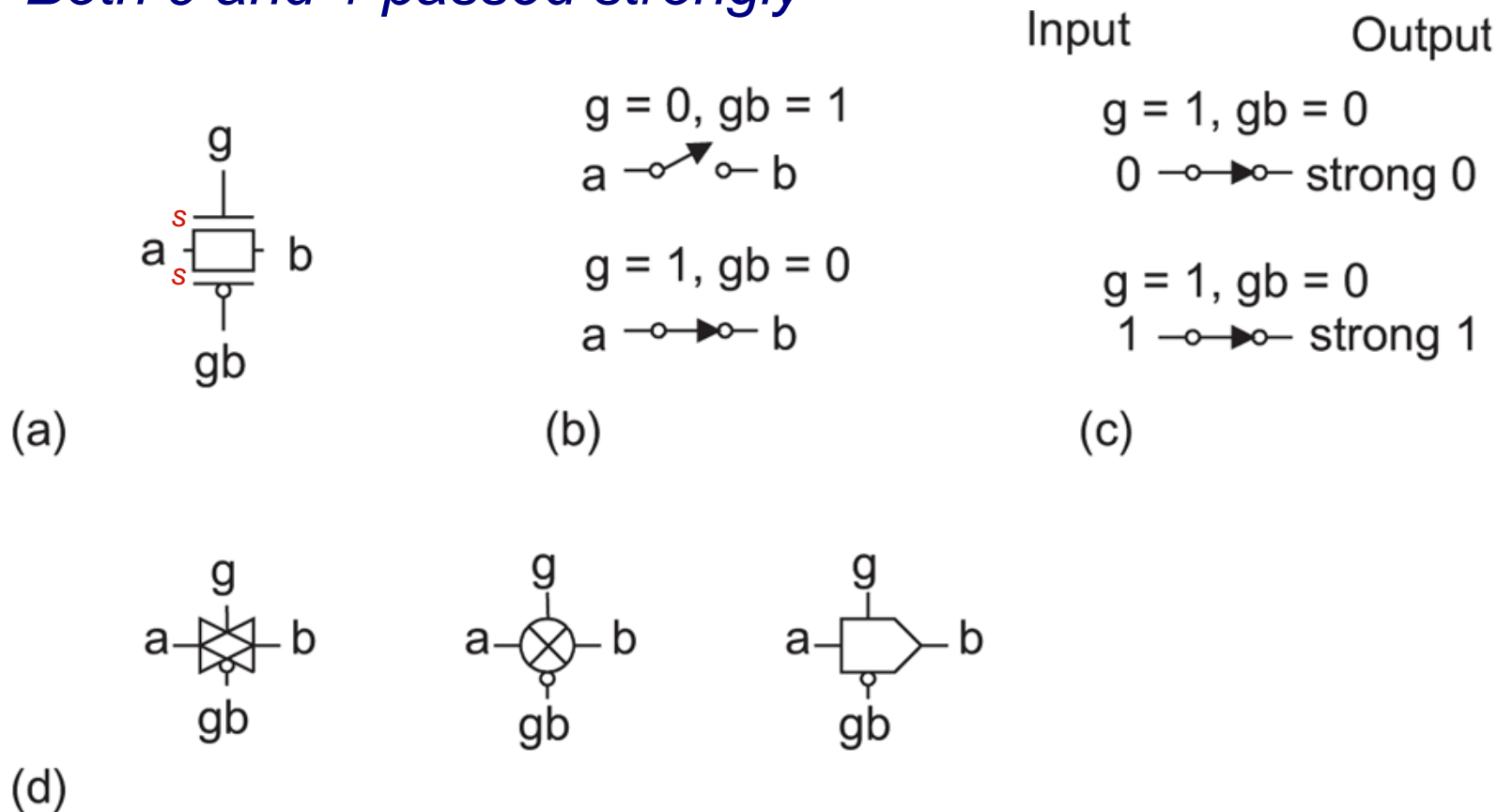


FIG 1.19 Pass transistor strong and degraded outputs

Transmission Gates: Pass Transistors in Parallel

Both 0 and 1 passed strongly



Double Rail Logic: both the control input and its complement is required

FIG 1.20 Transmission gate

Tristate Buffer

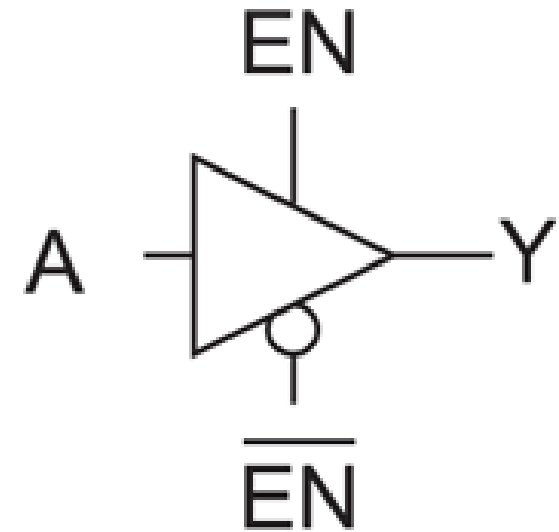
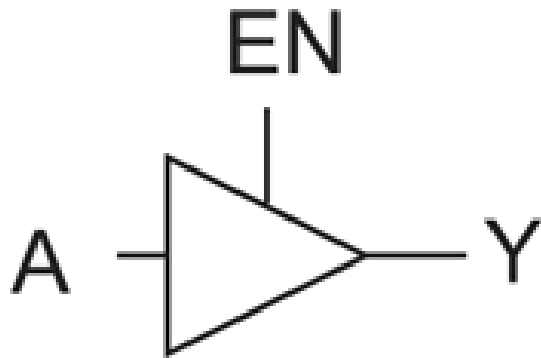


FIG 1.24 Tristate buffer symbol

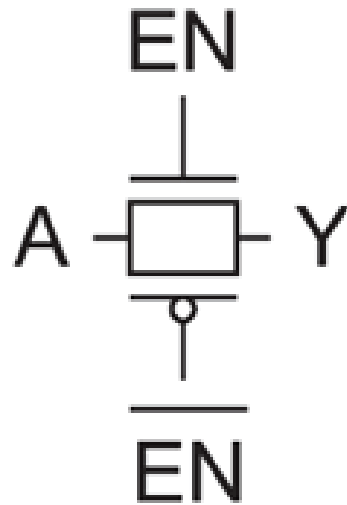
Tristate Buffer

Table 1.5 Truth table for tristate

EN / \overline{EN}	A	Y
0/1	0	Z
0/1	1	Z
1/0	0	0
1/0	1	1

Note: Z indicates a 'high-impedance' third state....

Transmission Gate as Tristate Buffer



Non-restoring: *input-signal will slowly degrade over a number of stages.... since Y is not connected to either Vdd or Gnd*

FIG 1.25

Transmission gate

Tristate Buffer as Inverter

Restoring: O/P (Y) is directly connected to **Vdd** or **GND**

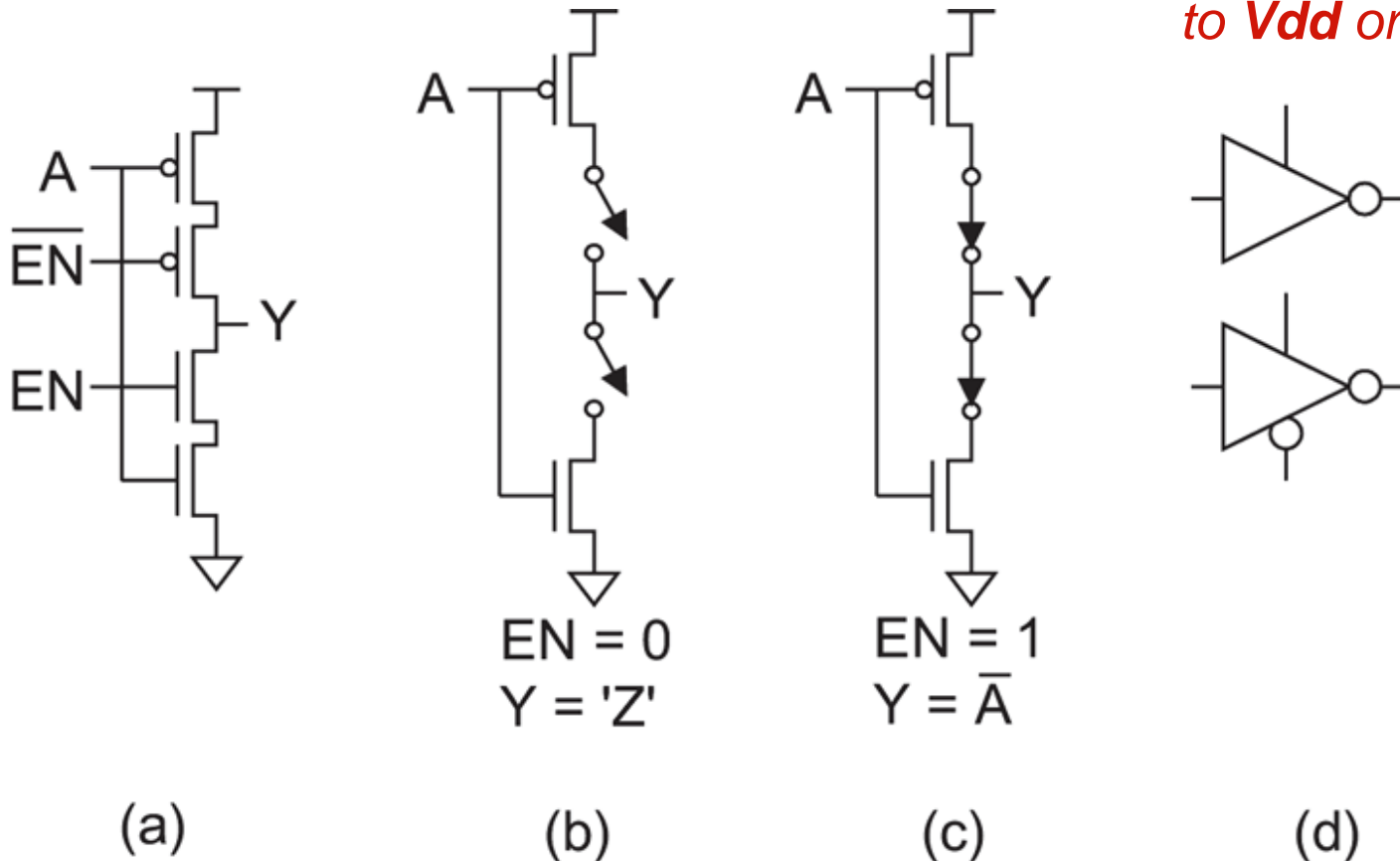


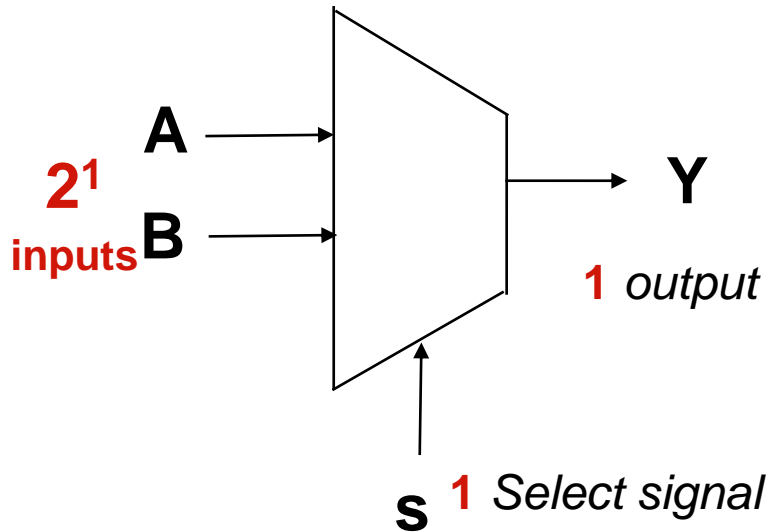
FIG 1.26 Tristate inverter

Multiplexer (MUX)

Connects **one** of n inputs to the **output**....

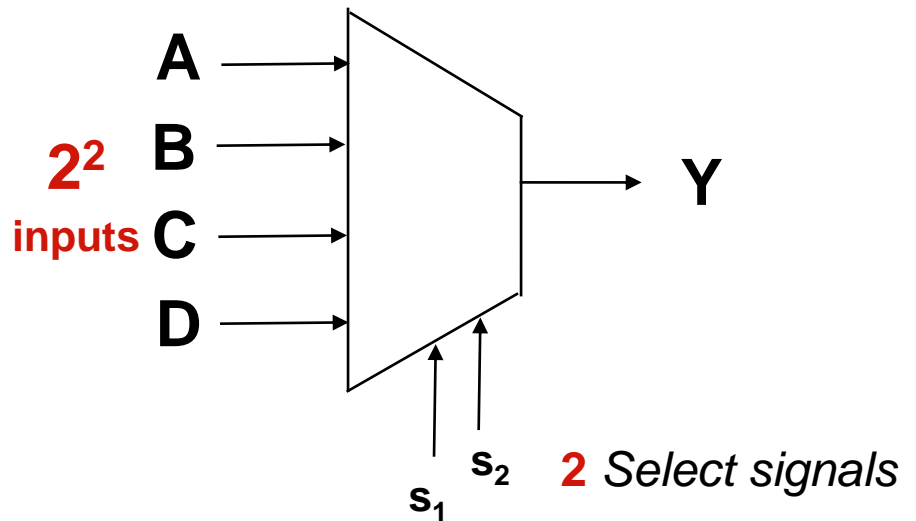
Used as data selectors...encoders

2:1 MUX



$$Y = As + Bs'$$

4:1 MUX



$$Y = As_1s_2 + Bs_1s_2' + Cs_1's_2 + Ds_1's_2'$$

In general, 2ⁿ inputs will have n select signals

$$Y = \sum_{k=0}^{2^n - 1} m_k I_k$$

m_k is a minterm of the n control variables and I_k is the corresponding data input

2:1 Multiplexer (MUX)

Table 1.6 Multiplexer truth table

s / \bar{s}	$D1$	$D0$	Y
0/1	X	0	0
0/1	X	1	1
1/0	0	X	0
1/0	1	X	1

$$Y = D1.S + D0.\bar{S} \text{ (when } s = 0, D1=X, \text{ when } \bar{s}=0, D0=X)$$

Note: X indicates a **don't care** condition

Non-restoring MUX

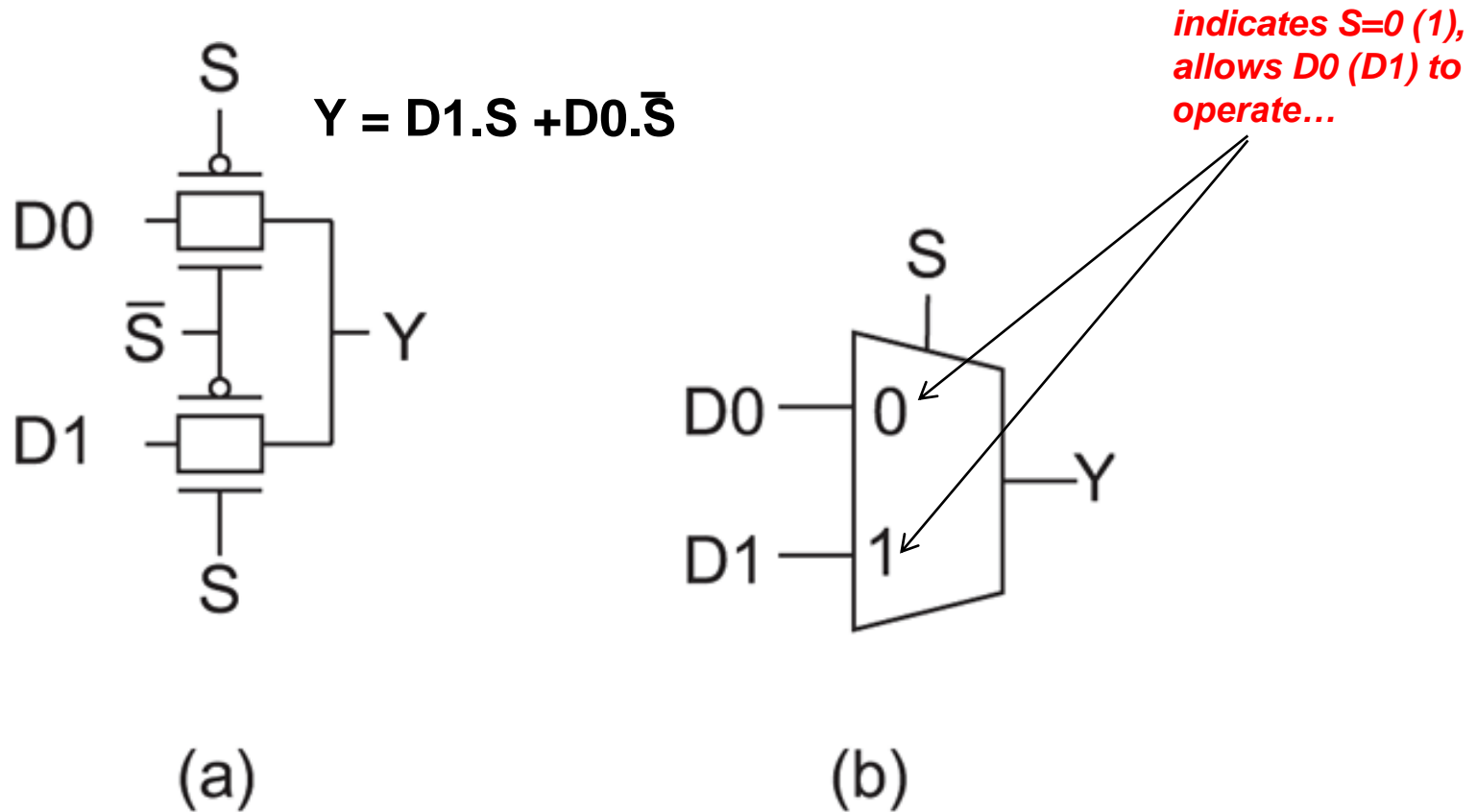


FIG 1.27 Transmission gate multiplexer

Inverting and Restoring MUX

$$\bar{Y} = D1.S + D0.\bar{S}$$

$$S/\bar{S} = 0/1$$

$$D0 = 0: Y = 1 = \bar{D0}$$

$$D0 = 1: Y = 0 = \bar{D0}$$

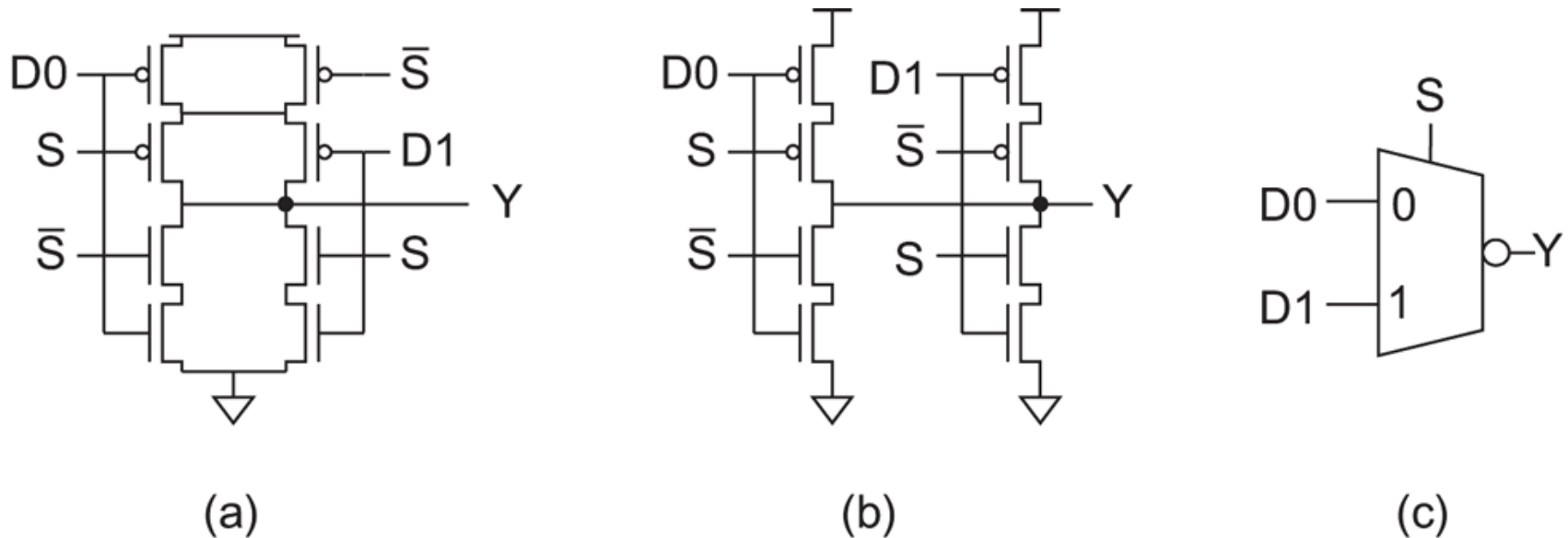
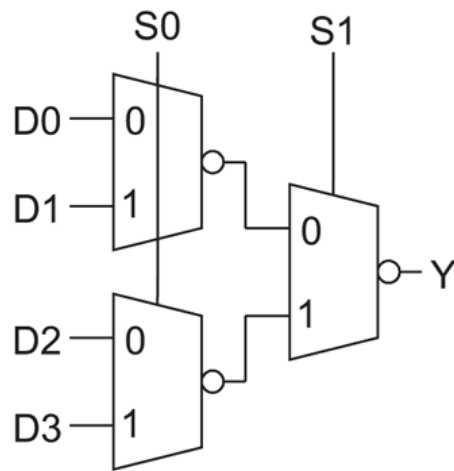
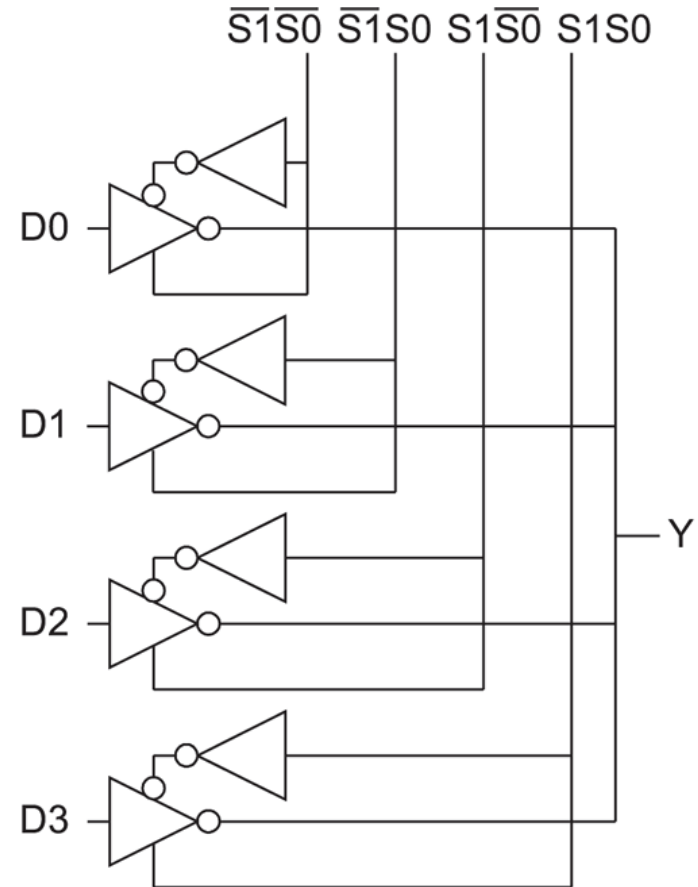


FIG 1.28 Inverting multiplexer

A 4:1 MUX



(a) Using three 2:1 MUXs



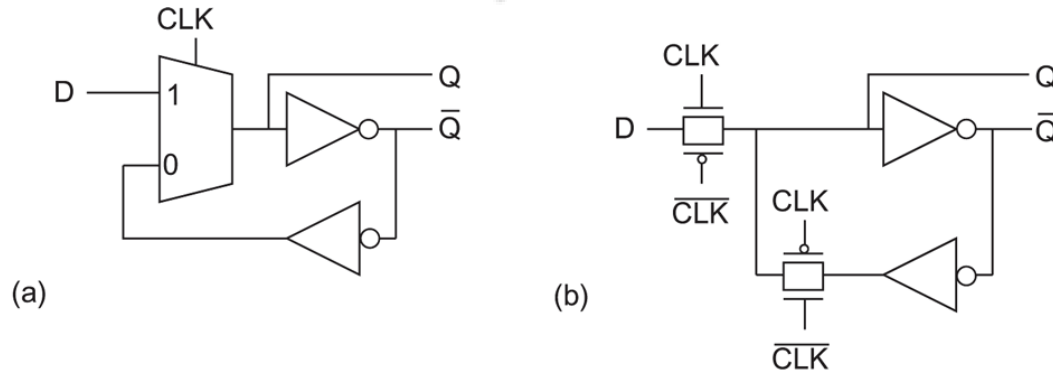
(b)

FIG 1.29 4:1 multiplexer

Static CMOS Summary

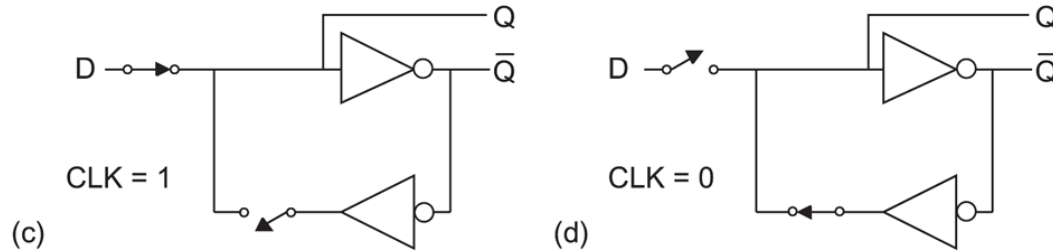
- ❑ In **static** circuits at every point in time (except when switching) the output is connected to either GND or V_{DD} via a low resistance path.
 - fan-in of n (or n -inputs) requires $2n$ (n N-type + n P-type) devices
- ❑ **Non-ratioed logic**: gates operate independent of PMOS or NMOS sizes (since no conflict between pull-up and pull-down networks)
- ❑ **No path** ever exists between **Vdd** and **GND**: **low static power**
- ❑ Fully-restored logic: (NMOS passes “0” only and PMOS passes “1” only)
- ❑ Gates must be **INVERTING**: $Y = \bar{X}$, so that $X=1$ (NMOS pull-down network is “ON”) for $Y=0$ (node is fully discharged)

Latches (level sensitive device)



CLK=1: D to Q

CLK=0: Holds state of Q



As long as CLK remains high: D to Q

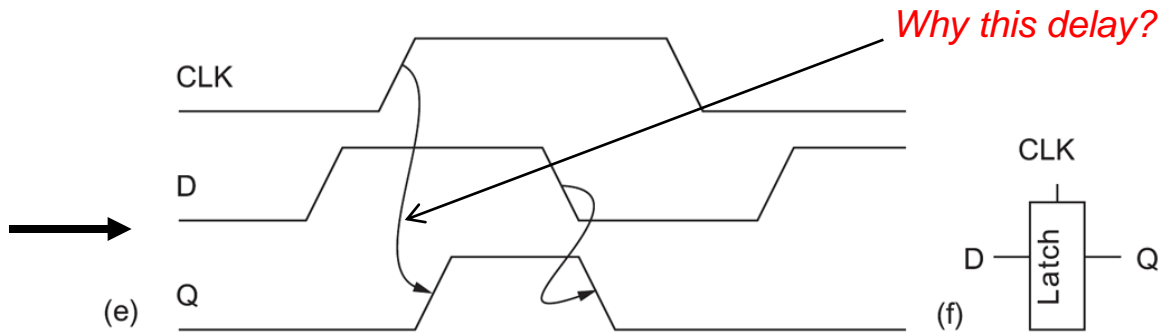


FIG 1.30 CMOS positive-level-sensitive D latch

Flip-Flops

(edge-triggered device)

Combines two latches:

One +ve sensitive (**slave**) and one -ve sensitive latch (**master**)

Edge Triggered FF or Master-Slave FF

$CLK=0$: D to QM

$$\overline{QM} = \overline{D}$$

Slave holds previous value of Q

$CLK=1$: master can't sample input and holds value of D

Slave opens and $QM=(D) = Q$

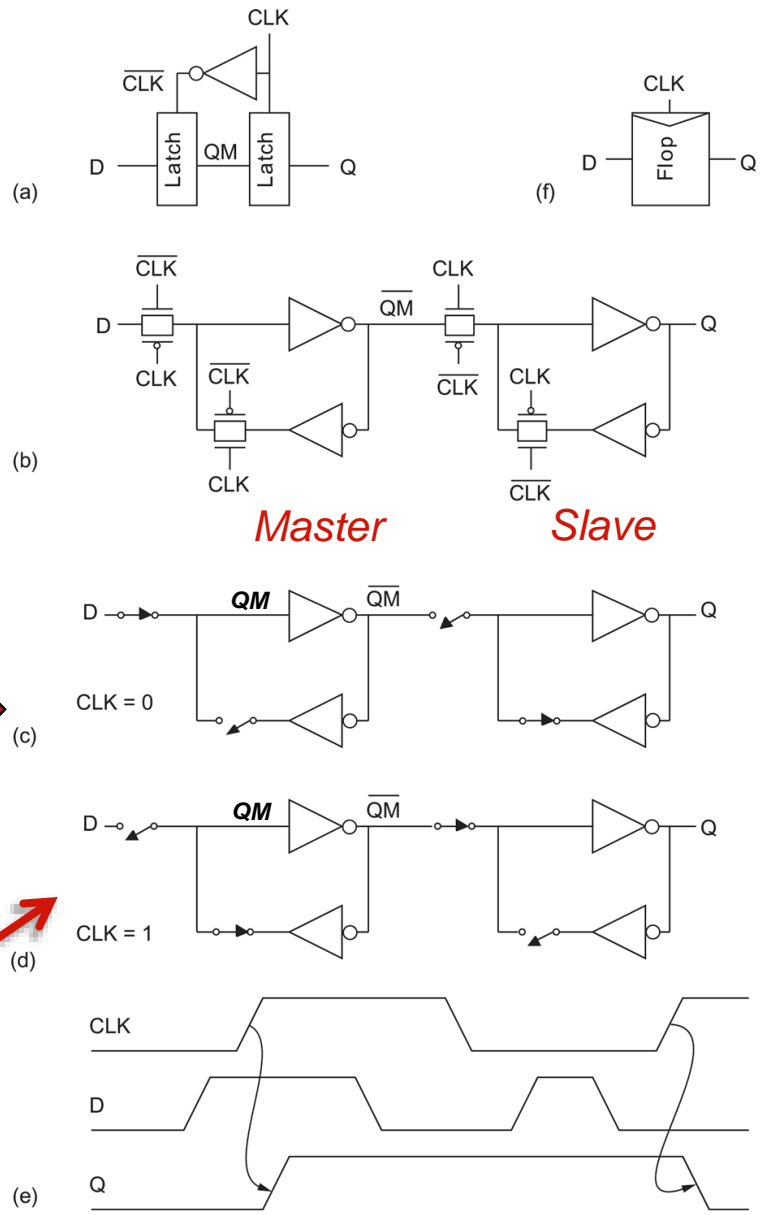
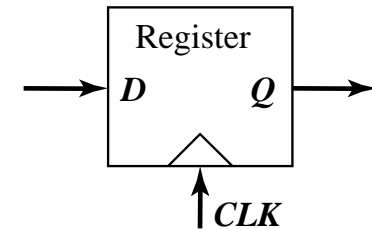
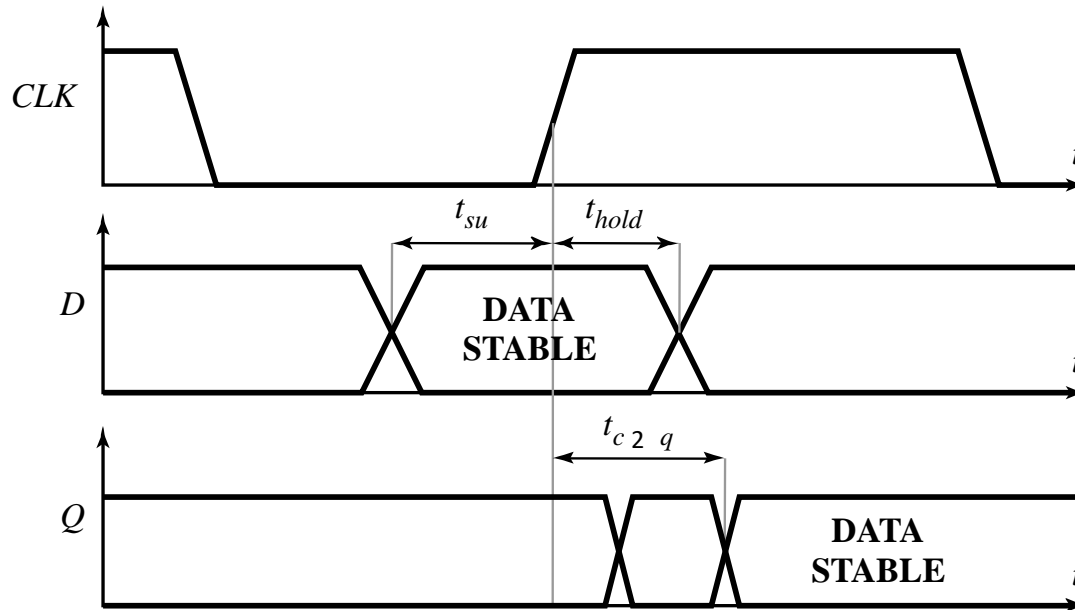


FIG 1.31 CMOS positive-edge-triggered D flip-flop

Timing Definitions



t_{su} = **setup time** = time for which the data inputs (D) must be valid before the CLK edge

t_{hold} = **hold time** = time for which data input must remain valid after the CLK edge

t_{c2q} = **worst case** propagation time through the Register (w.r.t the CLK edge)